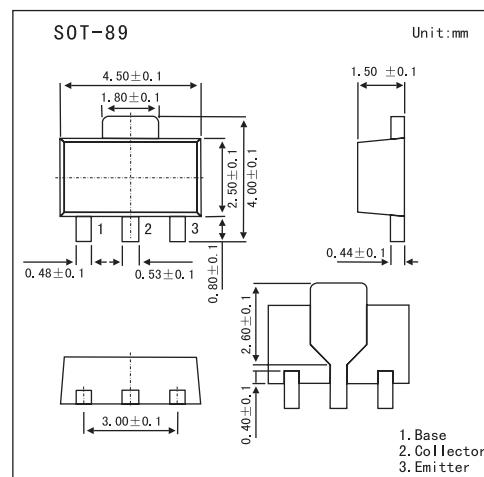


Small Signal Transistor

2SC5212

■ Features

- Low collector saturation voltage $V_{CE(sat)}=0.2V$ typ.
- High f_T $f_T=180MHz$ typ.
- Excellent linearity of dc forward current gain.
- High collector current $I_{CM}=1A$.
- Small package for mounting.

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	25	V
Emitter-base voltage	V_{EBO}	4	V
Collector-emitter voltage	V_{CEO}	20	V
Peak collector current	I_{CM}	1	A
Collector current	I_C	700	mA
Collector dissipation	P_C	500	mW
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	4			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=100\mu A, R_{BE}=\infty$	20			V
Collector cutoff current	I_{CBO}	$V_{CB}=25V, I_E=0$			1	μA
Emitter cutoff current	I_{EBO}	$V_{EB}=2V, I_C=0$			1	μA
DC current gain	h_{FE}	$V_{CE}=4V, I_C=100mA$	150		800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=25mA$		0.2	0.5	V
Gain bandwidth product	f_T	$V_{CE}=6V, I_E=-10mA$		180		MHz

■ h_{FE} Classification

Marking	UE	UF	UG
h_{FE}	150~300	250~500	400~800